## Carrier Dynamics and Multiple Exciton Generation in Nanocrystals: Applications to 3<sup>rd</sup> Generation Solar Photon Conversion

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Exciton dynamics, MEG
THz spectroscopy, MEG
SF,Exciton dynamics, MEG
Exciton dynamics, MEG (Si)
MEG photocurrent, QD arrays
THz Spectroscopy, QD arrays
MEG Solar Cells
Thermodynamic Efficiencies
Theory of MEG
Theory of MEG
Singlet Fission (SF)
Singlet Fission (Theory)

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#### **Consequences of Size Quantization**

- Large blue shift of absorption edge
- Discrete energy levels/structured absorption and photoluminescence spectra
- Dramatic variation of optical and electronic properties
- Enhanced photoredox properties for photogenerated electrons and holes
- Greatly enhanced exciton absorption at 300 K
- Conversion of indirect semiconductors to direct semiconductors or vice versa
- Greatly enhanced oscillator strength per unit volume (absorption coefficient

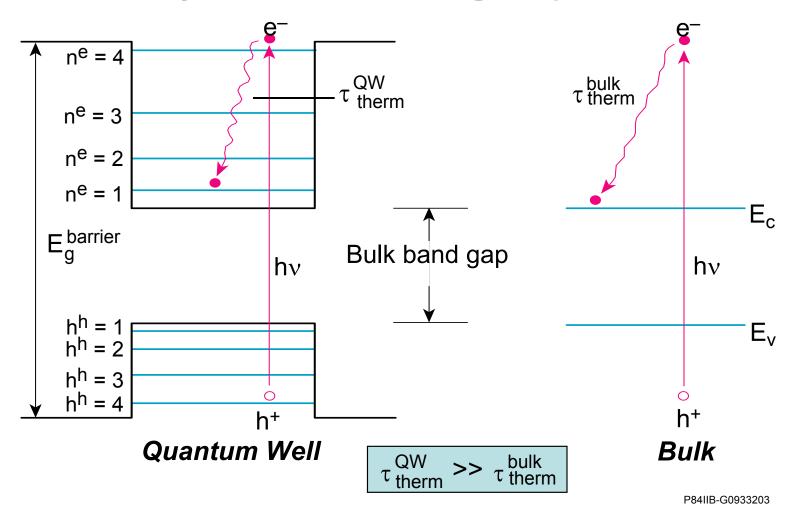
- Greatly modified pressure dependence of phase changes and direct to indirect transitions
- Greatly enhanced non-linear optical properties
- Efficient anti-Stokes luminescence

#### **Effects on Dynamics:**

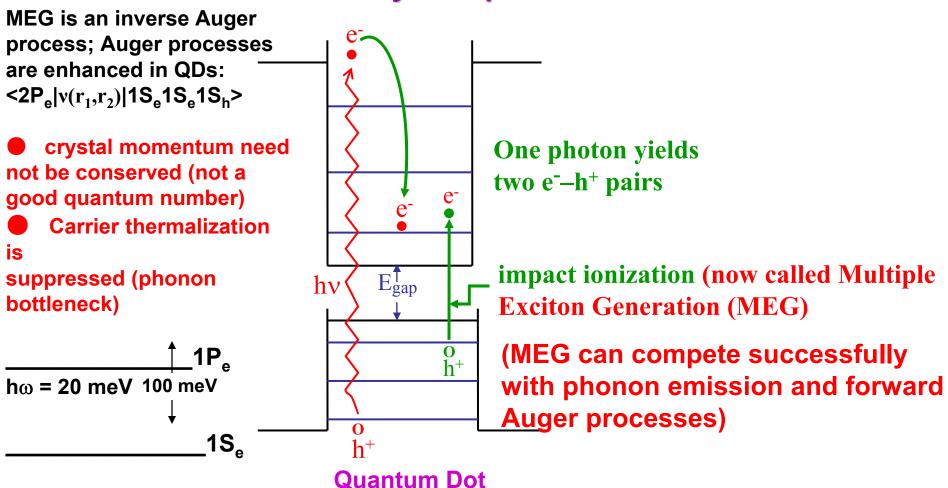
- Slowed relaxation and cooling (~10X) of photogenerated hot electrons and holes (excitons)
- Conservation of crystal momentum relaxed
- Enhanced Auger processes (invoked to explain PL blinking, breaking phonon bottleneck, and multiple exciton generation)

#### **QUANTIZATION EFFECTS**

- Auger processes enhanced
- Hot exciton cooling slowed (compared to MEG)
- Crystal momentum not a good quantum number



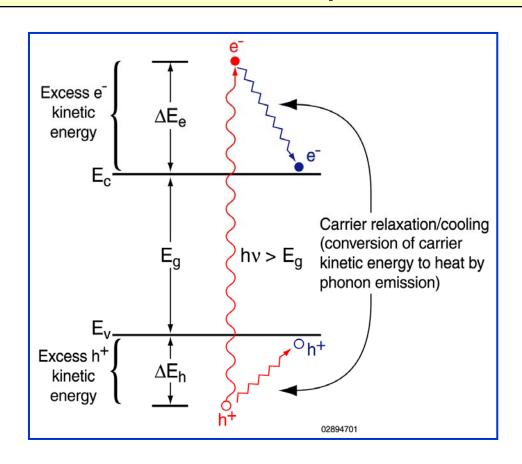
## Enhanced Photovoltaic Efficiency in Quantum Dot Solar Cells by Multiple Exciton Generation



A.J. Nozik, *Ann. Rev. Phys. Chem.* 52, 193, 2001; Physica E14,115, 2002; and in "*Next Generation Photovoltaics*", Marti& Luque, Eds, AIP, 2003;

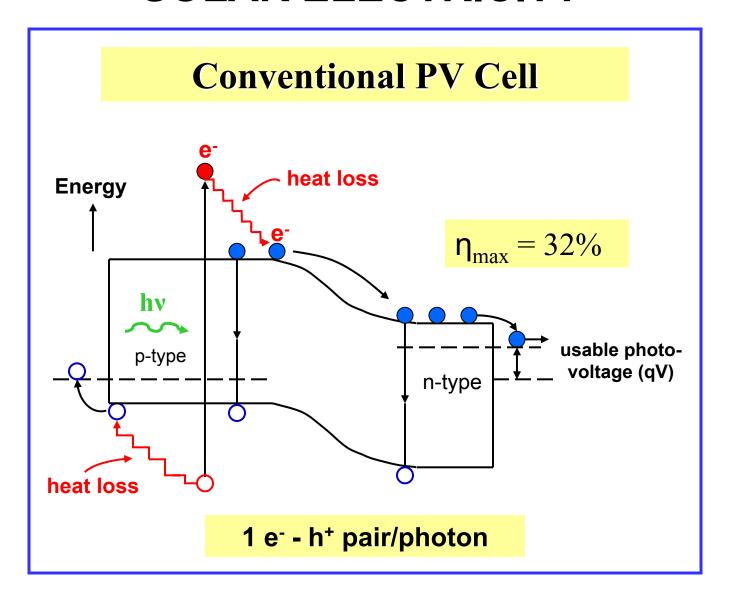
#### **Efficiency of Solar Photon Conversion**

# Main Process Limiting Conversion Efficiency (> 50% loss)



Hot e<sup>-</sup> Relaxation

#### **SOLAR ELECTRICITY**



## Photovoltaic Cells

- I. 1st Generation
  - Single crystal Si
  - Poly-grain Si

#### II. 2<sup>nd</sup> Generation (Polycrystalline Thin Film)

- Amorphous Si
- Thin film Si
- CulnSe<sub>2</sub>
- CdTe
- Dye-sensitized Photochemical Cell

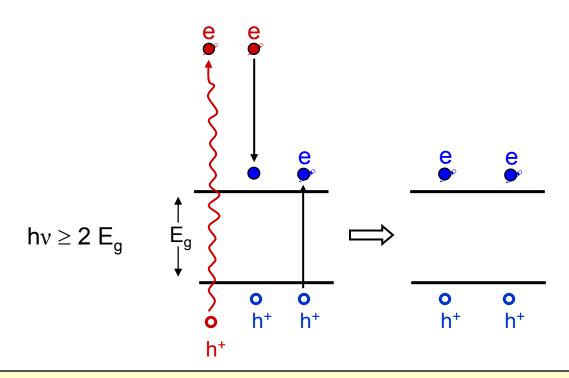
#### III. 3<sup>rd</sup> Generation (n<sub>theor</sub>>32% Queisser-Shockley limit and low cost)

- (High efficiency multi-gap tandem cells(here now but expensive))
- Multiple Exciton Generation (MEG) solar cells
- Quantum Dot Solar Cells
- Singlet Fission Solar Cells
- Hot electron converters
- Intermediate Band PV
- Photon management (upconversion and down conversion)
- Thermophotovoltaics/thermophotonics

See: M. Green, "Third Generation Photovoltaics". Springer, 2003, and Marti and A. Luque, "Next Generaton Photovoltaics", Inst. Of Physics Series in Optics and Optoelectronics, 2002

#### **Another Way**

#### Photocurrent Multiplication by Impact Ionization (I.I.)



1 photon yields 2 (or more) e<sup>-</sup> - h<sup>+</sup> pairs

(I.I. previously observed in bulk Si, Ge, InSb, PbS, and PbSe > 30 years ago—mainly with applied electric field (avalanche photodiodes)—BUT NOT USEFUL FOR PV BULK MATERIALS

#### **Detailed Balance Efficiency Calculations**

#### **Detailed balance model**

- -All photons above the bandgap are absorbed.
- -Photons less than the bandgap not absorbed.
- -Only loss if radiative recombination.
- -All photogenerated carriers are collected.

QY for carrier generation:

QY=0 E<Eg

QY = M MxEg<E<(M+1)Eg for M <Mmax, where Mmax=4/Eq

Photogenerated current:

 $Jg = q C IQY(E)\Gamma(E)dE$ 

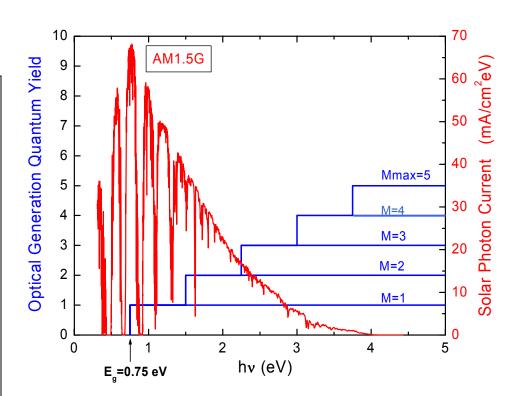
Recombination current:

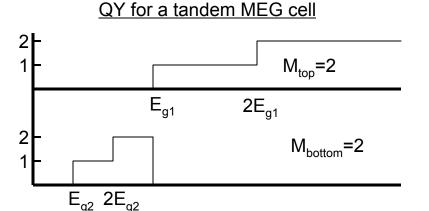
$$J_R(V, E_g) = qg \int_{E_g}^{\infty} \frac{QY(E)E^2}{\exp(\frac{E - qQY(E)V}{kT}) - 1} dE$$

IV curve:  $J(V)=J_g-J_R(V)$ 

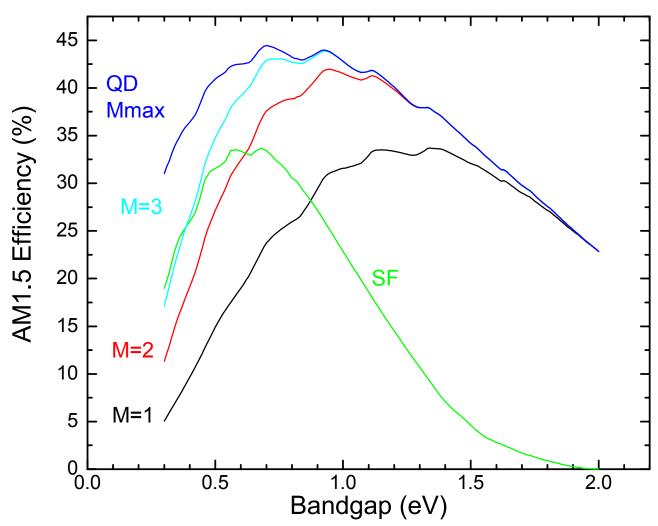
Series connected Tandem Cell:

$$J(V) = J_1(V_1) = J_2(V_2)$$
 and  $V = V_1 + V_2$ .



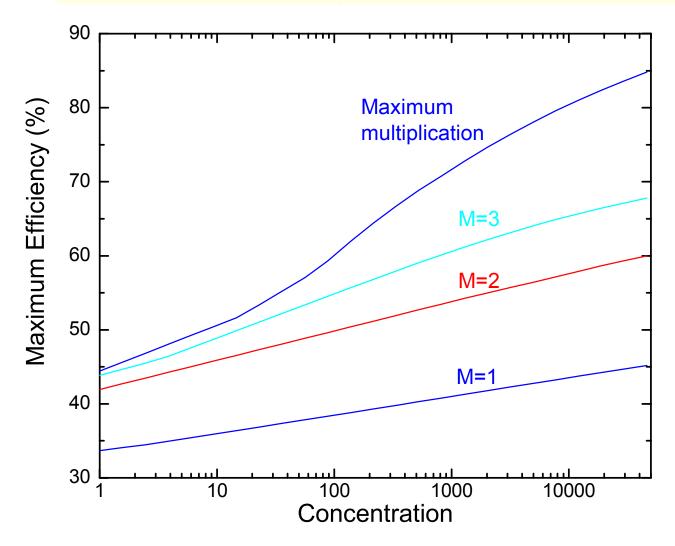


# Limiting Efficiency for Unconcentrated AM1.5G Spectrum (Single Bandgap)



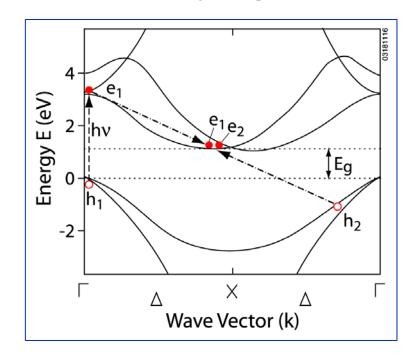
Hanna and Nozik, JAP 100, 74510 (2006)

#### RATE OF EFFICIENCY INCREASE WITH SOLAR CONCENTRATION



Single gap MEG cell efficiency increases at a faster rate under solar concentration than a normal semiconductor cell with no carrier multiplication (M=1).

#### **Bulk Si**



Queisser, et al. 1994

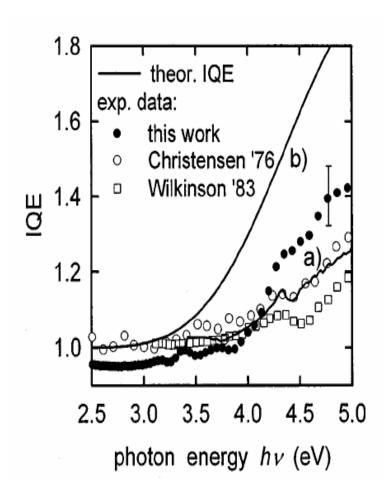
Conservation of energy E and momentum  $hk/(2\pi)$  is fulfilled if the two dash-dotted arrows add vectorially to zero.

QDs: Requirement for conservation of momentum is relaxed. Threshold should be lower.

# Quantum yield & IQE measurements

Si

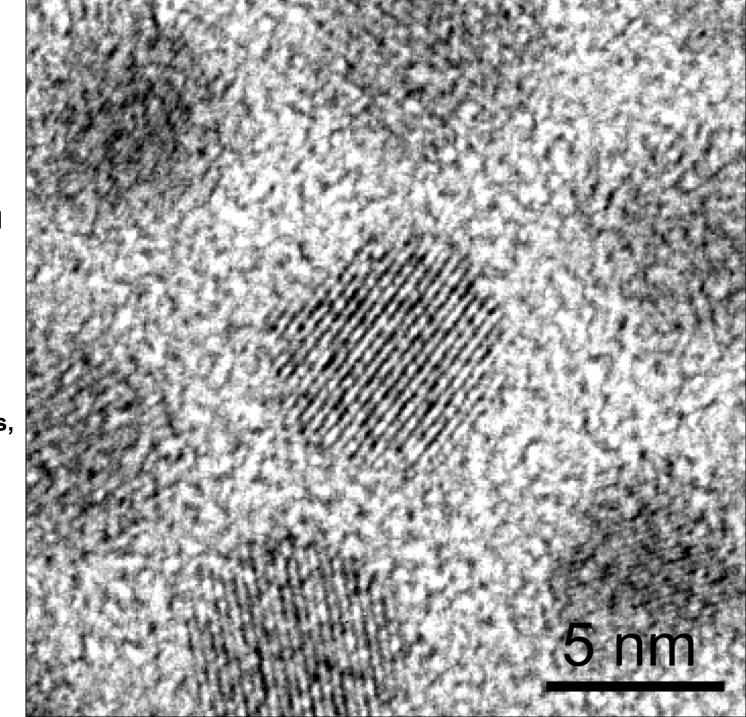
Because of the need to conserve momentum, and because the rate of impact ionization is much slower than the rate of phonon emission at low electron energies, impact ionization is an inefficient process in bulk semiconductors in the visible and near IR, and for Si requires UV photons.



Transmission
Electron Micrograph (TEM) of
PbSe Quantum
Dots (also called
(Nanocrystals)

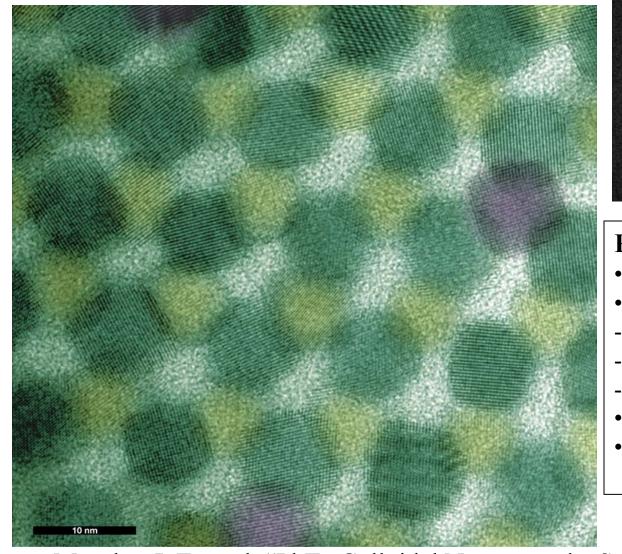
5 nanometers 5 x 10<sup>-9</sup> m 0.000005 mm

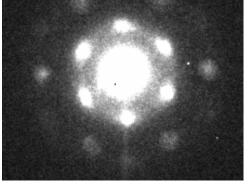
20 rows of atoms, ~ 6000 atoms, in these QDs



TEM From Andrew Norman

PbTe Arrays in HCP Configuration





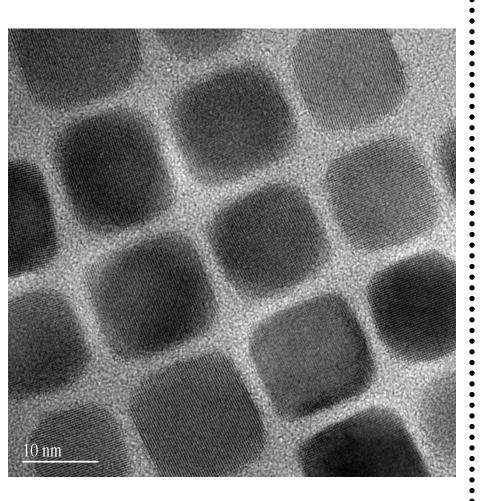
#### PbTe NCs

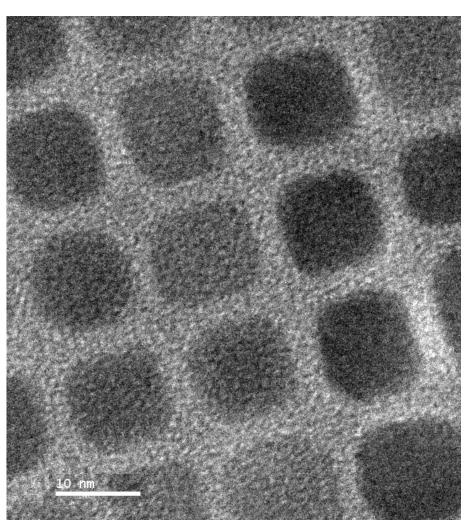
- •New Synthetic Routes
- •First optical characterization
- -absorption spectra
- -Photoluminescence
- -multiple exciton generation
- •Sphere to Cube Transition
- •Comparison of Lead Salt Properties

Murphy, J. E. et al. "PbTe Colloidal Nanocrystals: Synthesis, Characterization, and Multiple Exciton Generation." *J. Am. Chem. Soc.* **128**, 3241–3247 (2006).

TEM: Andrew Norman

# Arrays of Cubic-shaped Lead Salt PbSe : NCs PbTe

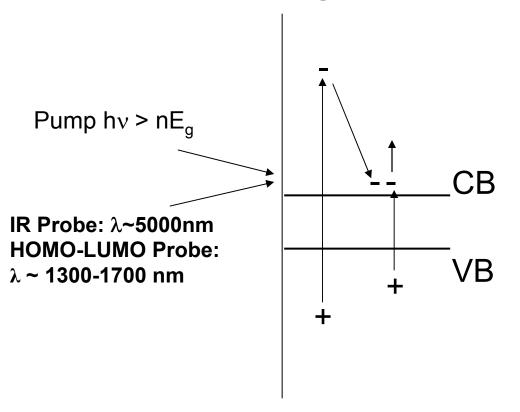




**TEM: Andrew Norman** 

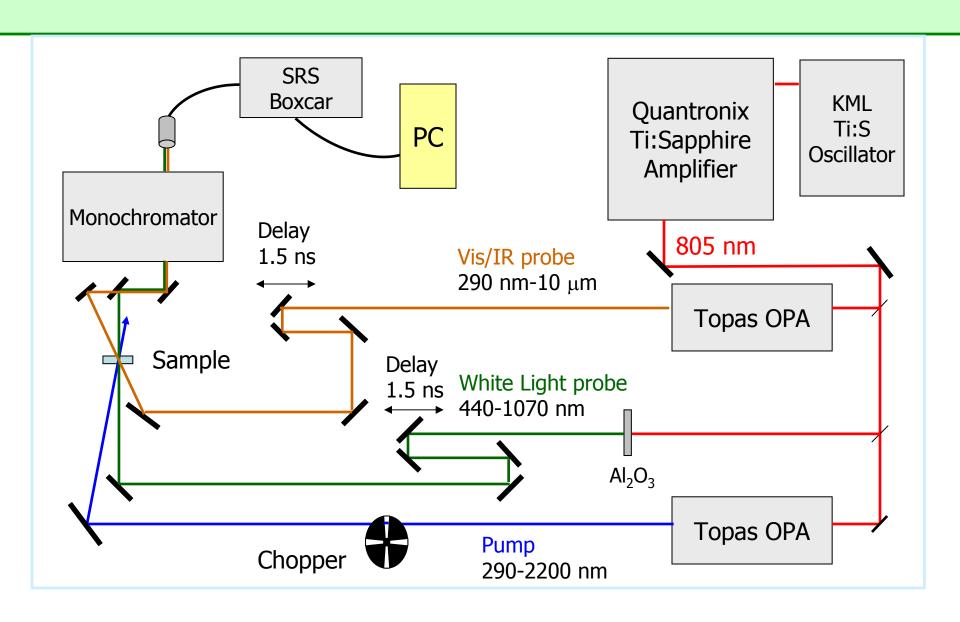
#### MEG DYNAMICS

Determine the photogenerated carrier density (QY) and thus MEG dynamics by: (a) measuring the free carrier absorption (IR probe) and exciton bleach (HOMO-LUMO probe); (b) measuring dynamics of multi-exciton decay vs single exciton decay, and the rise time of exciton bleaching and induced exciton absorption



Δα α e-h pair (exciton)
density; 1S bleach decay
dynamics = f(multiexciton
density); 1S bleach
dynamics and induced
exciton absorption
determine carrier cooling
rate and carrier
multiplication rate

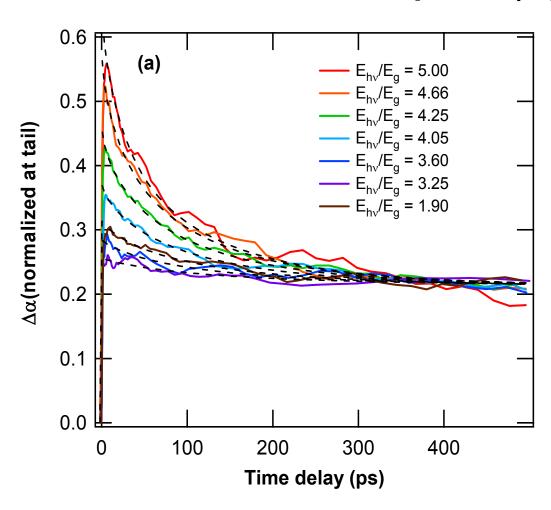
#### Transient absorption experimental setup



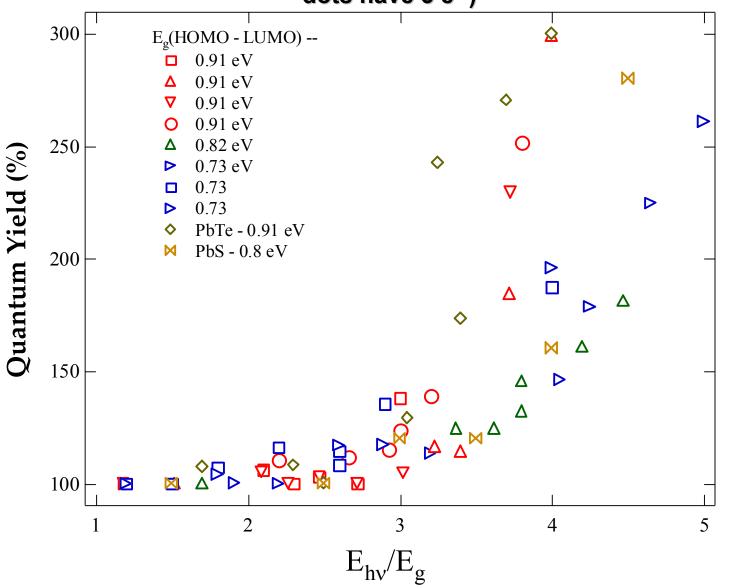
# Experimental Verification of Greatly Enhanced e-h+ multiplication (we term Multiple Exciton Generation (MEG)) in Quantum Dots

- R.D. Schaller and V.I. Klimov, Phys. Rev. Letts, 92, 186601 (May), 2004 (PbSe QDs)
- R.J. Ellingson, M. Beard, J. Johnson, P. Yu, O.Micic, A. Shabaev, A. Efros, A.J. Nozik, Nano Letters 5, 865, 2005 (PbSe and PbS QDs; 300% QY (3 e-/photon) at 4 times Eg)
- Recently, MEG also found in PbTe (NREL, JACS, 128, 3241, 2006) and CdSe (LANL, APL, 2005); 7 e<sup>-</sup>/photon in PbSe! (LANL, NanoLetts, 6, 424, 2006); InAs (Van Maekelbergh, Banin, et. Al., J. Phys. Chem. C (2007)); and Si (NREL, 2007)

## Exciton dynamics for different pump energies with mid-IR intraband probe (5 µ)



MEG in PbX; X = Se, S, Te
(QY > 200% means 3 e-/photon are created; QY = 300% means all dots have 3 e-)



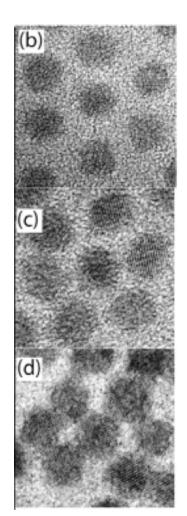
## Silicon Nanocrystals

- Particles 3-10 nm diameter
- Bulk bandgap 1.12 eV (~1100 nm);
- Si NC bandgaps 1.22-1.6 eV (1016 –

775 nm

TEM image courtesy of Innovalight, Inc.

## Amine soak properties

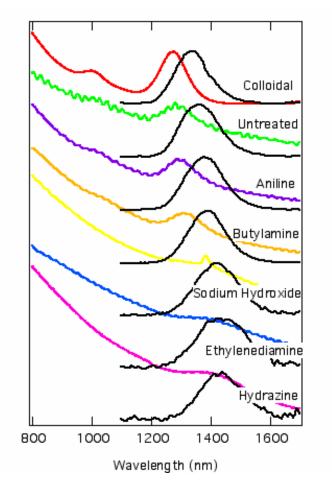


oleate

ligand	<i>d</i> (nm)	6	mobility (cm $^2$ V $^{-1}$ s $^{-1}$ )
ngand	(11111)	€ligand	(cm v s )
butlyamine	0.4	5.4	7.4
hydrazine	0.25	53	29.4
NaOH	0.1	1	35
ethylenediamine	0.4	16	47

aniline

ethylenediamine



Murphy, Beard, Nozik, JPC B 2006

#### PROPOSED NEW PHYSICS BASED ON MODEL INVOLVING:

# COHERENT SUPERPOSITION OF MULTI-EXCITON STATES IN SEMICONDUCTOR NANOCRYSTALS

Shabaev, Efros, Nozik, Nano Lett. 6, 2856 (2006)

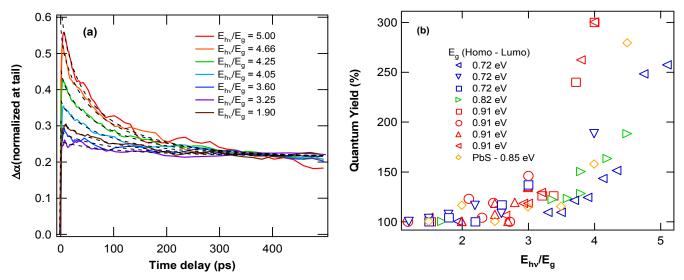
Other proposed models to explain MEG:

R.D. Schaller, V.M. Agranovich, and V.I. Klimov, *Nature Phys.* **1** (2005) p. 189.

A. Franceschetti, J.M. An, and A. Zunger, *Nano Lett.* **6** (2006) p. 2191.

### Multi-Exciton Generation by One Photon

#### **Efficient Multi-Exciton Generation in PbSe**



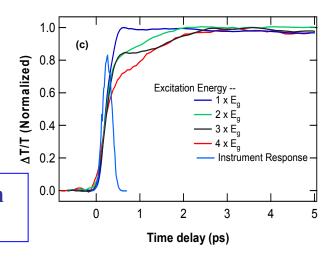
What is the reason of such high efficiency? - Impact Ionization?

#### Puzzle:

- Decay time ~100 ps (Auger process)
- •Rise time ~ < 2-3 ps (Inverse Auger process)

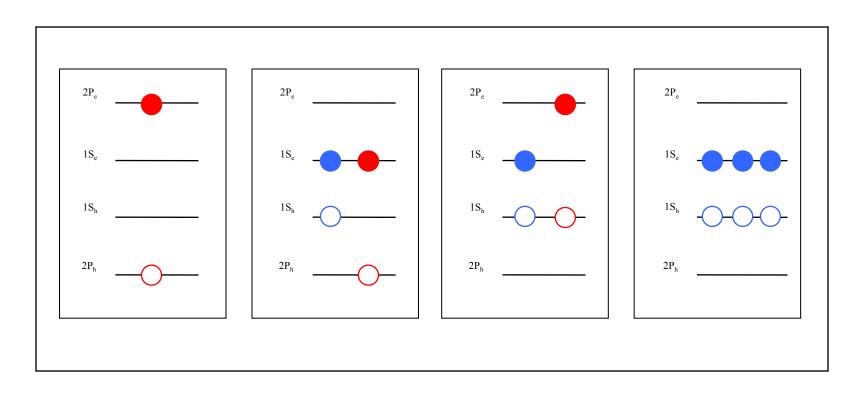
Instantaneous creation of a coherent superposition of several electron-hole pairs by a single photon

R.Ellingson, et.al. NanoLetters TBP



#### **NEW MODEL FOR MEG**

#### Coherent Superposition of Multi-Excitonic States in PbSe QDs

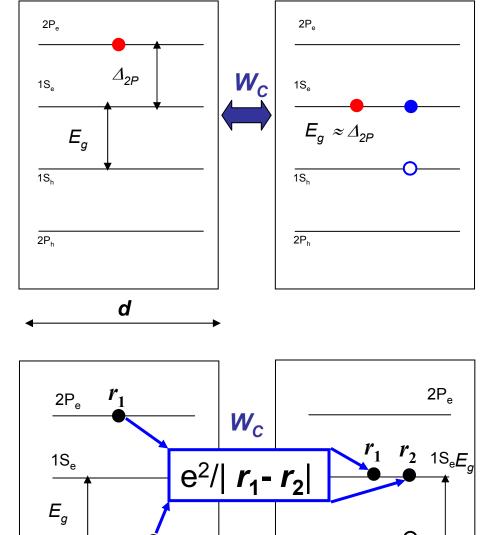


#### States with Energy Larger than Energy

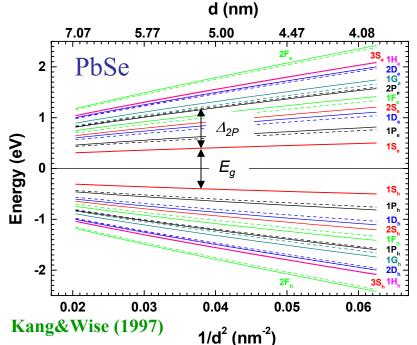
Gap

 $1S_h$ 

Electron in NC occupying 2P<sub>e</sub> state:



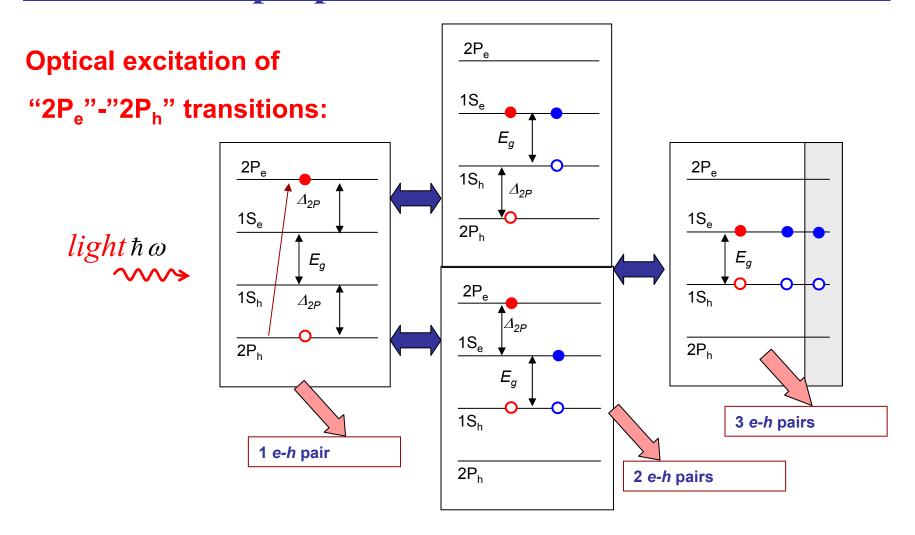
 $1S_h$ 



Two states are degenerate and coupled:

$$W_{C} = \langle 2P_{e} | v(r_{1}, r_{2}) | 1S_{e} 1S_{e} 1S_{h} \rangle$$

#### **Coherent Superposition of Multi-Exciton States**



The efficiency of the multi-exciton generation depends on the relaxation mechanism.

There is high probability that the state relaxes to the two *e-h* pair state.

## **Density matrix**

Theoretical description requires:

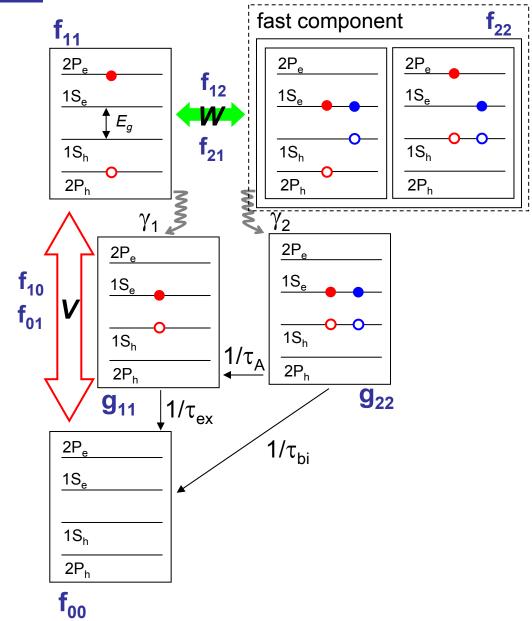
time dependent density matrix for:

- Short pulse excitation
- •Different relaxation mechanisms

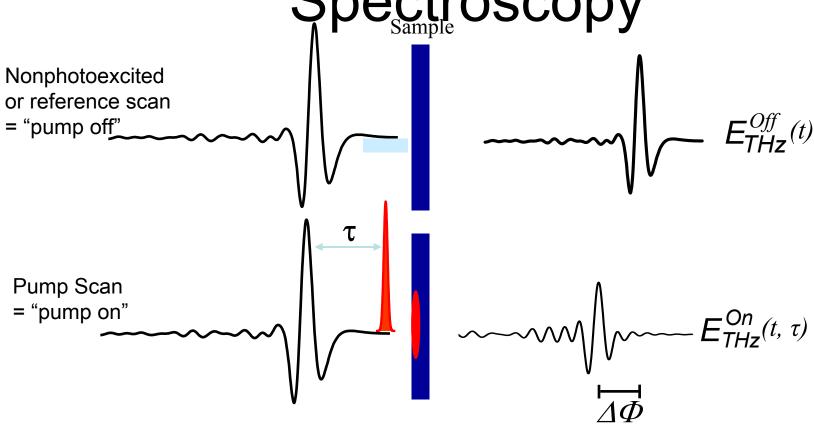
$$\frac{\partial \rho}{\partial t} = \frac{i}{\hbar} [\rho H]$$

Dynamics for times:  $\Delta t << \tau_{\text{A}} << \tau_{\text{r}}$ 

(Shabaev, Efros, Nozik, Nano Lett. 6, 2856 (2006)



# Time Resolved THz Spectroscopy

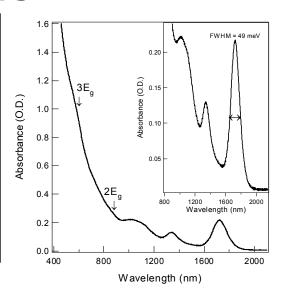


$$\frac{\Delta E_{THz}(t,\tau)}{E_{THz}^{Off}(t)} \cong \frac{-\sigma(\tau)x}{2cn\varepsilon_o}$$

- •Measure transient THz frequency average conductivity
- •Subpicosecond resolution
- Mechanistic information
- •No electrical contacts

## Film Treatments

Treatment	d(nm)	$\mathcal{E}_{arsigma}$	$n_{ave}$	$\mu$ (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> )
		S	arc	. ,
Oleic Acid	1.8	2	1.57	
Aniline	0.8	2	2.2	
Butlyamine	0.4	5.4	2.46	7.4
ethylenediamine	0.4	16	2.62	47.0
hydrazine	0.25	52	2.69	29.4
NaOH	0.1	1	2.4	35.0



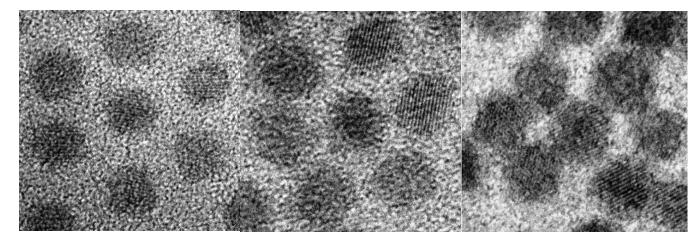
Oleate Cap  $CH_3(CH_2)_7HC=CH(CH_2)_7COOH$  D ~ 1.8 nm

Aniline Cap

D ~ 0.8 nm

Ethylenediamine H<sub>2</sub>NCH<sub>2</sub>CH<sub>2</sub>NH<sub>2</sub>

D = < 0.4 nm



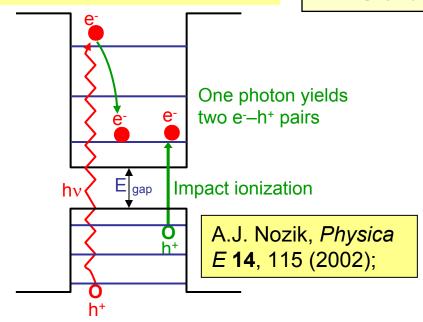
### Quantum Dot Solar Cells

# Potential Major Advantages of Using Quantum Dots

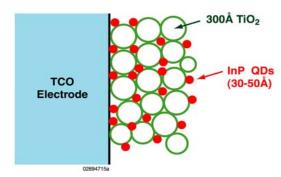
- Enhanced photocurrent multiplication by MEG (Inverse Auger Process
- Hot electron transport through minibands in QD arrays
- Slowed Cooling of High Energy (Hot)
   Electrons (phonon bottleneck)

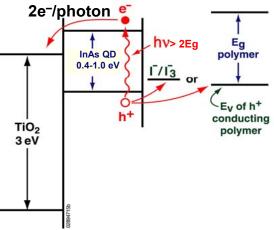
Enhanced Photovoltaic
Efficiency in Quantum Dot
Solar Cells by Inverse Auger
Effect (Impact Ionization)

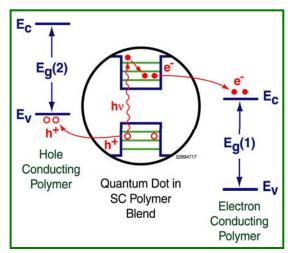
## **Quantum Dot Solar Cells**



QD-Sensitized Nanocrystalline TiO<sub>2</sub> Solar Cell

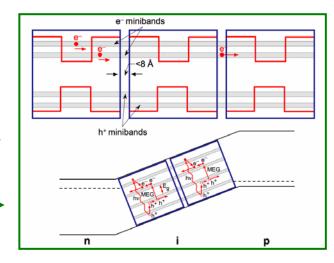




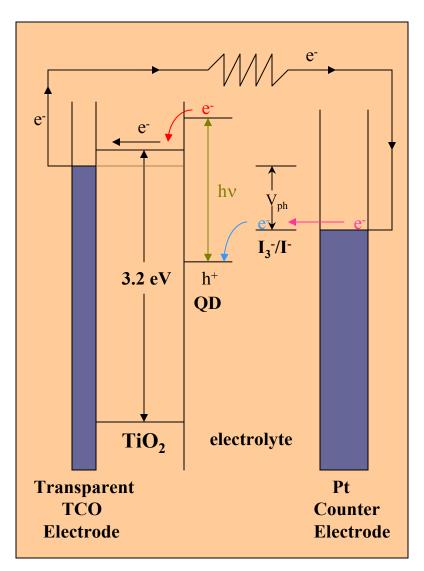


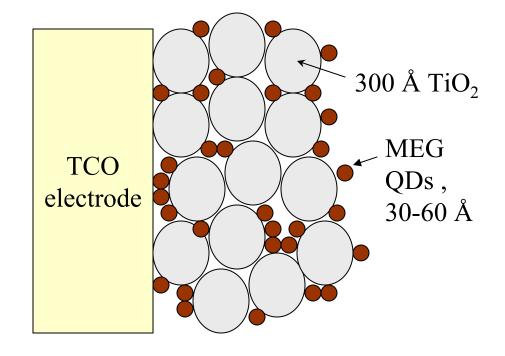
QD-Conducting Polymer Blend Solar Cell

> p-i-n QD Array Solar Cell



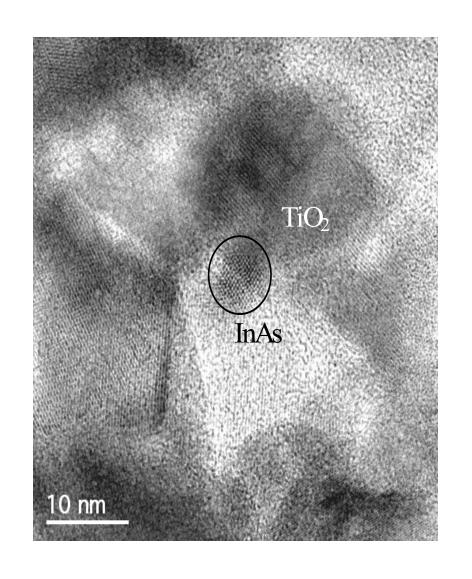
## Quantum Dot Sensitized TiO<sub>2</sub> Solar Cell

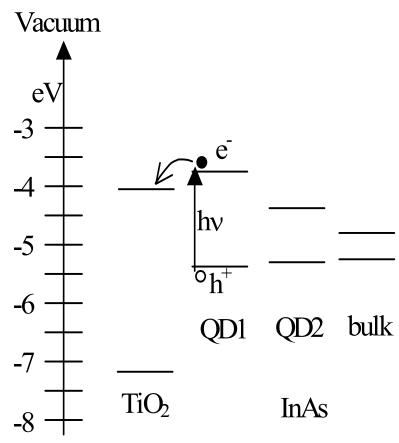




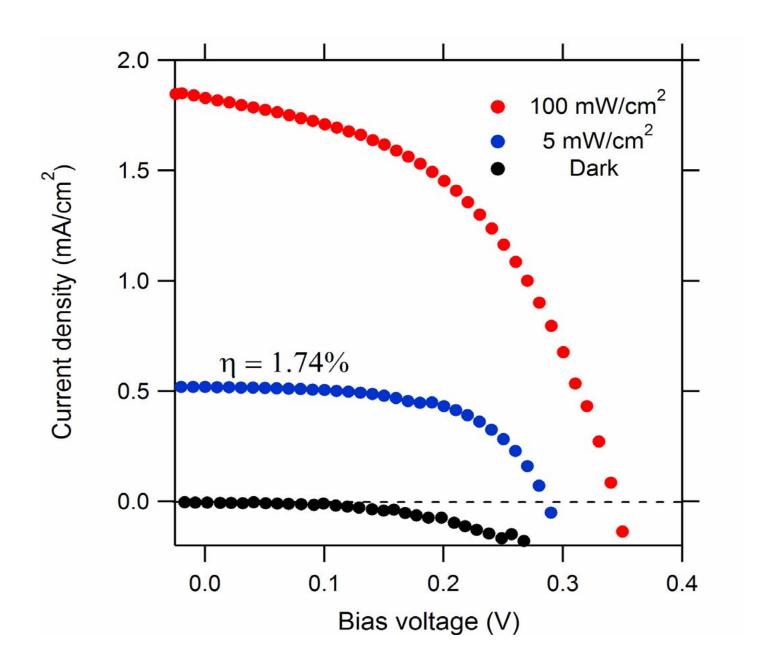
- -Analogous to dye-sensitized TiO<sub>2</sub> solar cells
  - -10 to 20  $\mu$ m film of NC TiO<sub>2</sub> (10-30 nm)
  - -Ru dyes ⇒ Efficiency ~ 11%
- -Advantages of QD's as sensitizers:
  - -possibility of slowed hot e- cooling
  - -possibility of impact ionization
  - -tunable absorption

#### InAs QD Solar Cell Based on NC TiO<sub>2</sub>

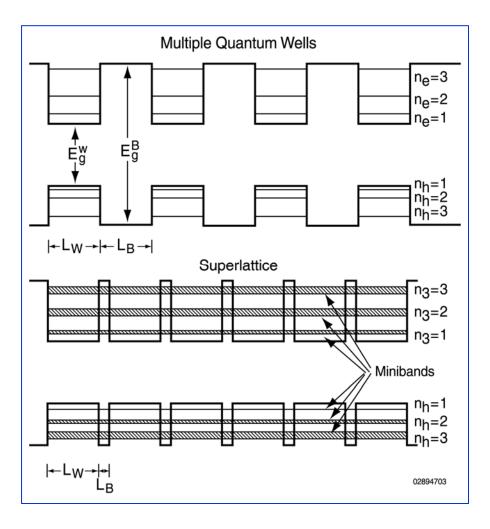




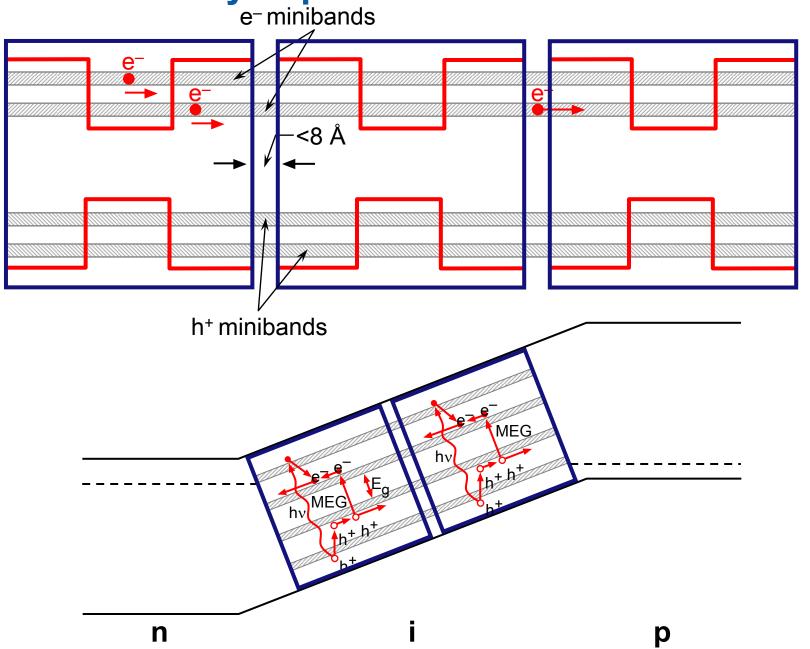
#### J-V Characteristic for 3.4 nm InAs QD Sensitized Solar Cell



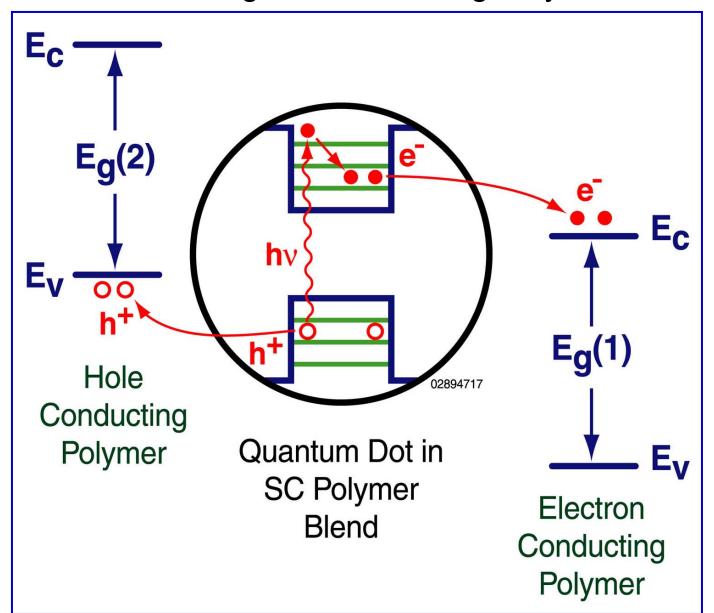
# Miniband Formation in 1-D Confined Quantum Films



#### QD Array in p-i-n Photon Conversion Cell



## PV Cell Based on QDs Dispersed in n-and p-type Organic Conducting Polymers



#### **Summary/Conclusions**

- Size quantization in semiconductors may greatly affect the relaxation dynamics of photoinduced carriers. These include:
  - slowed hot electron relaxation (partial phonon bottleneck)
  - enhanced Auger process (MEG)
- The theoretical and measured energy threshold for impact ionization in bulk semiconductors (e.g. Si, InAs, GaAs) is 4-5 times the band gap. Much lower thresholds are predicted for QDs because of the relaxation of the need to conserve momentum. The rate of exciton multiplication is also expected to be much faster in QDs (Auger processes  $\alpha$  1/d $^6$ )
- Very efficient exciton multiplication experimentally observed in PbSe, PbTe, PbS, InAs, and Si QDs; the threshold photon energy is 2Eg. Up to 3 electrons per photon (300% QY) have been observed at sufficiently high photon energies ( $\geq 4E_g$ ). A new model based on coherent superposition of multiexcitonic states is introduced to explain these results. Two excitons/photon yield over 90% of the efficiency benefit of carrier multiplication.
- Singlet fission is the molecular analog of MEG and also could yield enhanced solar photon conversion efficiencies. It had been observed in dimeric diphenylisobenzofurane. Single gap cells with carrier multiplication with MEG yield the same improvement for PV as 2-gap tandem PV cells. A tandem cell with SF and/or MEG is required to improve maximum efficiency for H2O splitting. Higher efficiency in SF cells for PV require a tandem cell configuration.

#### **Summary/Conclusions - Continued**

- Various configurations of Quantum Dot Solar Cells are suggested that could yield high conversion efficiencies:
  - 1. Nanocrystalline TiO2 sensitized with QDs
  - 2. QD arrays exhibiting 3-D miniband formation
- 3. QDs embedded in a polymeric blend of electron- and hole-conducting polymers.
- 4. SF molecular chromophores in a tandem cell for PV and photoelectrolysis
  - THE DYNAMICS OF HOT ELECTRON and EXCITED MOLECULE COOLING, FORWARD AND INVERSE AUGER RECOMBINATION (MEG), AND ELECTRON TRANSFER CAN BE MODIFIED IN QD AND SF SYSTEMS TO POTENTIALLY ALLOW VERY EFFICIENT SOLAR PHOTON CONVERSION VIA EFFICIENT MULTIPLE EXCITON GENERATION